## NSN 5961-01-048-7734

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Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:
Plastic
Overall Length:
Between 0.240 inches and 0.290 inches
Overall Height:
Between 0.030 inches and 0.080 inches
Overall Width:
Between 0.115 inches and 0.160 inches
Component Name And Quantity:
2 transistor
Mounting Method:
Press fit
Features Provided:
Burn in and hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
40.0 collector to base voltage, dc all transistor and 15.0 collector to emitter voltage, dc all transistor and 5.0 emitter to base voltage, dc all
transistor
Current Rating Per Characteristic:
500.00 milliamperes source cutoff current all transistor
Power Rating Per Characteristic:
350.0 milliwatts small-signal input power, common-collector absolute all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius ambient air
Special Features:
All transistor junction pattern arrangement: npn
Terminal Type And Quantity:
6 ribbon
Shelf Life:
N/a
Unit Of Measure:
<del></del>
Demilitarization:
No
Fiig: